## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

: 6,959,157 B2

Page 1 of 1

DATED

: October 25, 2005

INVENTOR(S) : Toshiki Nakayama

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

## Column 8,

Line 42, "211 -R" should read -- 211-R --.

## Column 9,

Line 51, "capacitance" should read -- capacitor --.

## Column 10,

Line 41, "NMQS" should read -- NMOSFET --.

Signed and Sealed this

Twenty-fifth Day of April, 2006

JON W. DUDAS
Director of the United States Patent and Trademark Office